

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-14: (Withdrawn)

Claims 15-29: (Cancelled)

30. (Previously Presented) A fluid ejecting device comprising:
a silicon substrate having a <100> crystalline orientation;
a plurality of fluid drop generators formed on a first surface of said silicon substrate;
a fluid feed slot extending from a second surface of said silicon substrate to said first surface;
said fluid slot formed by deep reactive ion etching to a depth of at least one-half a thickness of the silicon substrate followed by anisotropic wet etching, and having an opening at the first surface having a width W1 that is less than a width W2 of an opening at the second surface.

31. (Cancelled)

32. (Currently Amended) [The fluid ejecting device of claim 15] A fluid ejecting device comprising:
a silicon substrate having a <100> crystalline orientation;
a plurality of fluid drop generators formed on a first surface of said silicon substrate;
a fluid feed slot extending from a second surface of said silicon substrate to said first surface;
said fluid slot formed by deep reactive ion etching followed by anisotropic wet etching, and having an opening at the first surface having a width W1 that

is less than a width W2 of an opening at the second surface, wherein said fluid feed slot was formed by deep reactive ion etching to a depth of at least one-half of a thickness of the substrate.

33. (Currently Amended) [The fluid ejecting device of claim 15] A fluid ejecting device comprising:

a silicon substrate having a <100> crystalline orientation;

a plurality of fluid drop generators formed on a first surface of said silicon substrate;

a fluid feed slot extending from a second surface of said silicon substrate to said first surface;

said fluid slot formed by deep reactive ion etching followed by anisotropic wet etching, and having an opening at the first surface having a width W1 that is less than a width W2 of an opening at the second surface, wherein said fluid feed slot was formed by deep reactive ion etching to a depth of at least about 475 micrometers.

34. (Cancelled).

35. (Currently Amended) [The fluid ejecting device of claim 34] A fluid ejecting device comprising:

a silicon substrate having a <100> crystalline orientation;

a plurality of fluid drop generators formed on a first surface of said silicon substrate;

a fluid feed slot extending from a second surface of said silicon substrate to said first surface;

said fluid slot formed by deep reactive ion etching followed by anisotropic wet etching, and having an opening at the first surface having a width W1 that is less than a width W2 of an opening at the second surface, wherein the substrate has a thickness of about 675 micrometers or less; and

wherein said fluid feed slot was formed by deep reactive ion etching to a depth of at least one-half of a thickness of the substrate.

36. (Currently Amended) [The fluid ejecting device of claim 34] A fluid ejecting device comprising:

a silicon substrate having a <100> crystalline orientation;

a plurality of fluid drop generators formed on a first surface of said silicon substrate;

a fluid feed slot extending from a second surface of said silicon substrate to said first surface;

said fluid slot formed by deep reactive ion etching followed by anisotropic wet etching, and having an opening at the first surface having a width W1 that is less than a width W2 of an opening at the second surface, wherein the substrate has a thickness of about 675 micrometers or less; and

wherein said fluid feed slot was formed by deep reactive ion etching to a depth of at least about 475 micrometers.

37. (Previously Presented) The fluid ejecting device of claim 35 wherein:
W1 is about 100 micrometers; and
W2 is about 300 micrometers.

38. (Currently Amended) [The fluid ejecting device of claim 15] A fluid ejecting device comprising:

a silicon substrate having a <100> crystalline orientation;

a plurality of fluid drop generators formed on a first surface of said silicon substrate;

a fluid feed slot extending from a second surface of said silicon substrate to said first surface;

said fluid slot formed by deep reactive ion etching followed by anisotropic wet etching, and having an opening at the first surface having a width W1 that is less than a width W2 of an opening at the second surface.

wherein the substrate has a thickness STH;
said fluid feed slot was formed by deep reactive ion etching to a depth DD, with an angle of re-entrancy α ; and
 $W1$ equals about $W2 + 2(DD \cdot \tan \alpha + (DD - STH / \tan(54.7 \text{deg.})))$.

39. (Previously Presented) The fluid ejecting device of claim 38 wherein said fluid feed slot was formed by deep reactive ion etching to a depth of at least one-half of a thickness of the substrate.

40. (Previously Presented) The fluid ejecting device of claim 38 wherein $W1$ is about 100 micrometers or less.

41. (Previously Presented) The fluid ejecting device of claim 38 wherein $W2$ is about 300 micrometers or less.

42. (Previously Presented) The fluid ejecting device of claim 38 wherein:
 $W1$ is about 100 micrometers or less; and
 $W2$ is about 300 micrometers or less.

43. (Previously Presented) The fluid ejecting device of claim 38 wherein said angle of re-entrancy α is about 5 deg.

44. (Previously Presented) A fluid ejecting device comprising:
a silicon substrate having a $\langle 100 \rangle$ crystalline orientation and a thickness STH;
a plurality of fluid drop generators formed on a first surface of said silicon substrate;
a fluid feed slot extending from a second surface of said silicon substrate to said first surface;
said fluid slot being formed at least in part by deep reactive ion etching to a depth DD, with an angle of re-entrancy α , and having an opening at

the first surface having a width $W1$ that is less than a width $W2$ of an opening at the second surface, wherein $W1$ equals about $W2 + 2(DD \cdot \tan \alpha + (DD - STH / \tan(54.7 \text{deg.})))$.

45. (Previously Presented) The fluid ejecting device of claim 44 wherein said angle of re-entrancy α is about 5 deg.

46. (Previously Presented) The fluid ejecting device of claim 44, wherein DD is more than one half of STH .

47. (Previously Presented) The fluid ejecting device of claim 44 wherein $W1$ is about 100 micrometers or less.

48. (Previously Presented) The fluid ejecting device of claim 44 wherein $W2$ is about 300 micrometers or less.

49. (Previously Presented) The fluid ejecting device of claim 44 wherein $W1$ is about 100 micrometers or less and $W2$ is about 300 micrometers or less.